



BCH65S04D4

Silicon Carbide Schottky Diode

650V, 4A

Description

BCH65S04D4 utilizes Bestirpower's advanced silicon carbide diode technology. This technology combines the benefits of excellent low forward voltage and robustness. Consequently, the family is suitable for application requiring high power efficiency

Benefits

- High frequency
- Low heat dissipation requirements
- Reduce size and cost of the system
- High-reliability

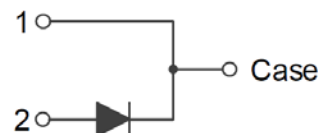
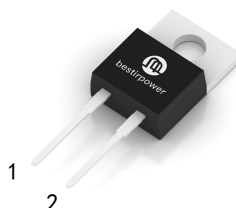
Applications

- Switch mode power supply
- Solar inverter
- Data Center
- Uninterruptible power supply

Features

V_{RRM}	I_F	T_C	Q_C
650 V	4 A	142 °C	7.9

- Negligible reverse recovery
- High-speed switching
- Positive Temperature Coefficient
- Temperature-Independent Switching
- RoHS compliant



Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage		650	V
I_F	Forward Current	$T_C = 25^\circ\text{C}$	10	A
		$T_C = 130^\circ\text{C}$	5.5	A
		$T_C = 142^\circ\text{C}$	4	A
$I_{F,SM}$	Non-Repetitive Forward Surge Current	$T_C = 25^\circ\text{C}, t_p = 10 \text{ ms}$	32	A
		$T_C = 110^\circ\text{C}, t_p = 10 \text{ ms}$	22	A
$I_{F,RM}$	Repetitive Peak Forward Surge Current	$T_C = 25^\circ\text{C}, t_p = 10 \text{ ms}$	23	A
I^2dt value	$\int I^2 dt$	$T_C = 25^\circ\text{C}, t_p = 10 \text{ ms}$	5.1	A^2s
		$T_C = 110^\circ\text{C}, t_p = 10 \text{ ms}$	2.6	A^2s
P_{tot}	Power Dissipation	$T_C = 25^\circ\text{C}$	49	W
		$T_C = 110^\circ\text{C}$	21	W
		$T_C = 150^\circ\text{C}$	8	W
T_J, T_{STG}	Operating Junction and Storage Temperature		-55 to +175	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Typ.	3.06	$^{\circ}C/W$

Electrical Characteristics ($T_C = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{DC}	DC blocking voltage		650			V
V_F	Forward Voltage	$I_F=4A, T_J=25^{\circ}C$	-	1.4	1.6	V
		$I_F=4A, T_J=175^{\circ}C$	-	1.97	2.2	
I_R	Reverse Current	$V_R = 650\text{ V}, T_J = 25^{\circ}C$	-	1	50	μA
		$V_R = 650\text{ V}, T_J = 175^{\circ}C$	-	30	100	
Q_C	Total Capacitive Charge	$V_R = 400\text{ V}, T_J = 25^{\circ}C$	-	7.9	-	nC
C	Total Capacitance	$V_R = 0\text{ V}, f = 1\text{MHz}$	-	119	-	pF
		$V_R = 200\text{ V}, f = 1\text{MHz}$	-	14.24	-	
		$V_R = 400\text{ V}, f = 1\text{MHz}$	-	13.64	-	
E_C	Capacitance Stored Energy	$V_R = 400\text{ V}, T_C = 25^{\circ}C$	-	1.9	-	μJ

Typical Performance Characteristics

Figure 1. Forward Characteristics

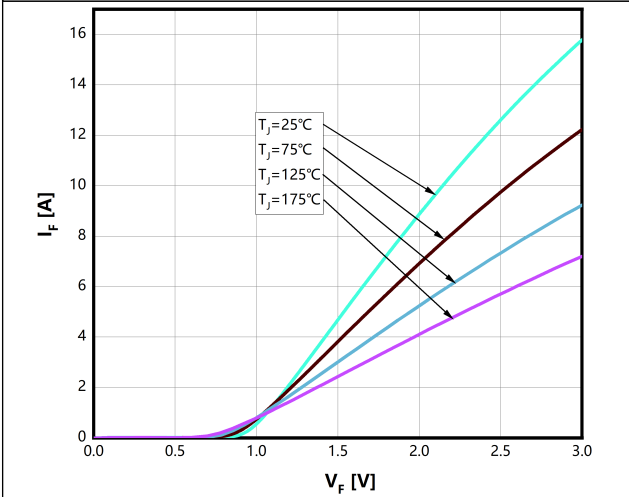


Figure 2. Reverse Characteristics

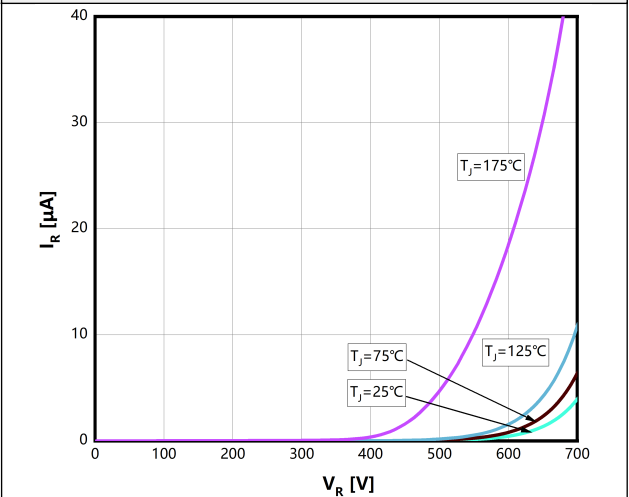


Figure 3. Capacitance vs. Reverse Voltage

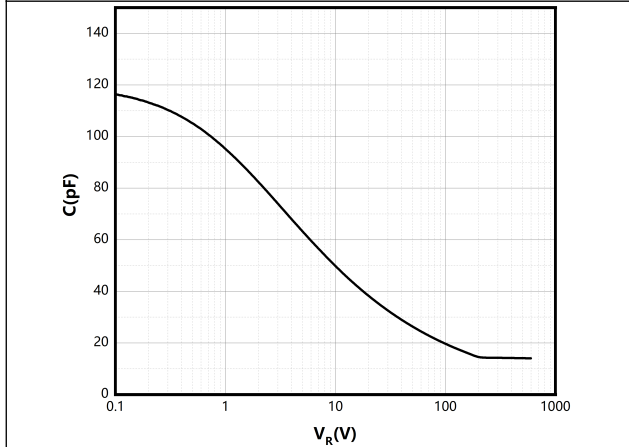


Figure 4. Capacitance Charge vs. Reverse Voltage

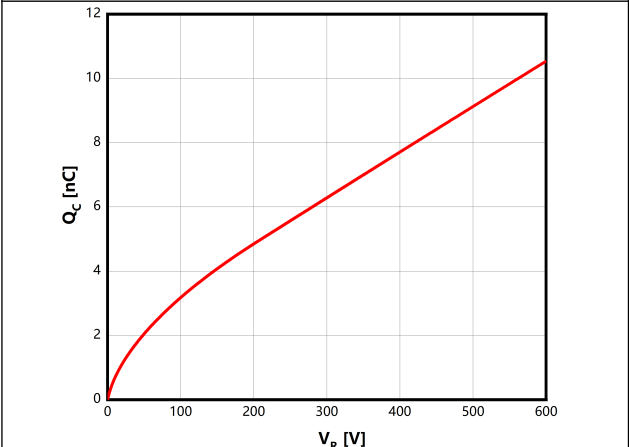


Figure 5. Capacitance Stored Energy

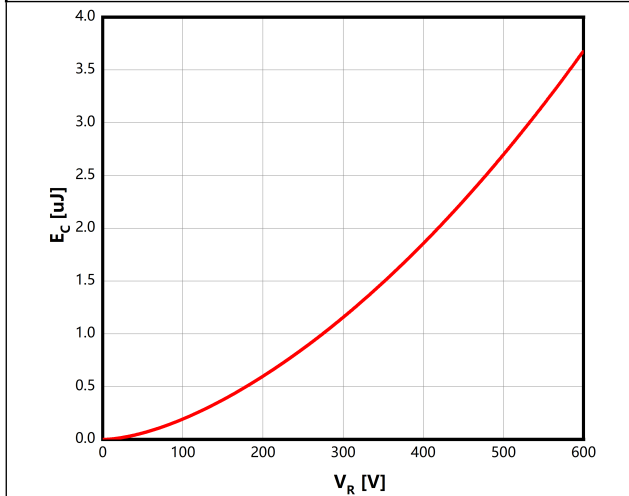
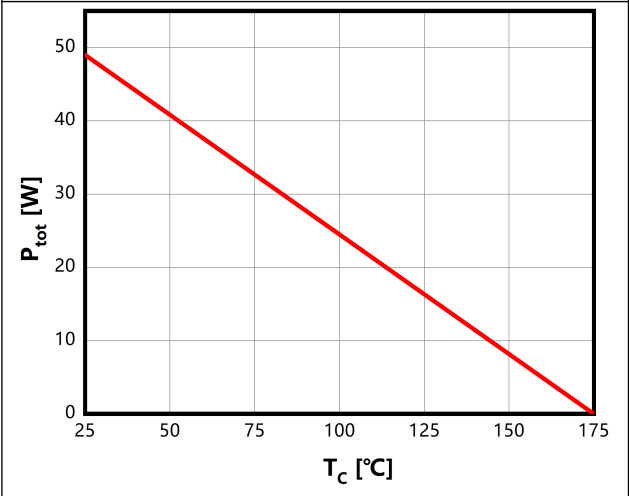


Figure 6. Power Derating



Typical Performance Characteristics

Figure 7. Current Derating

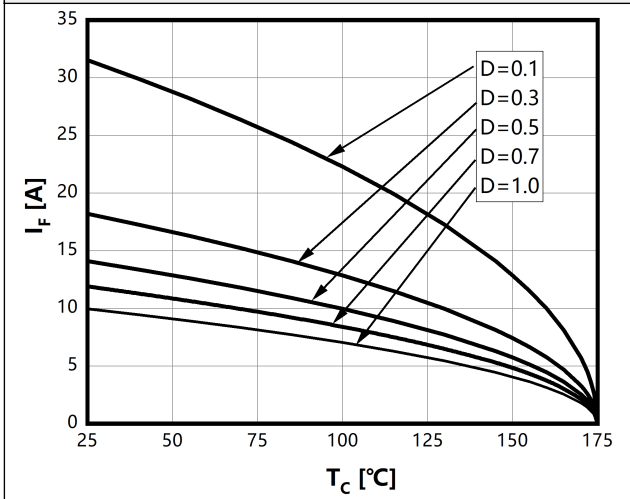
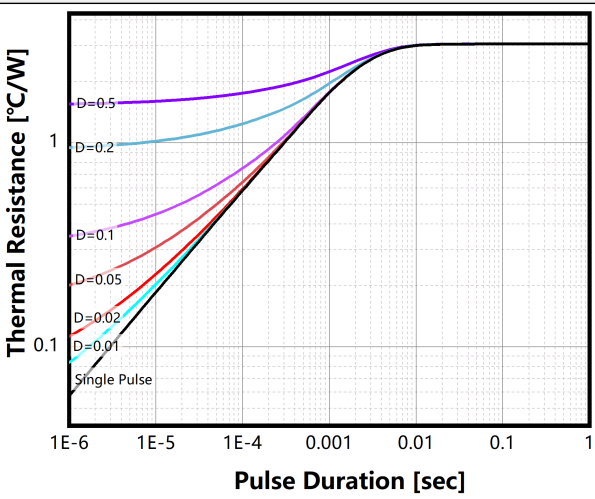
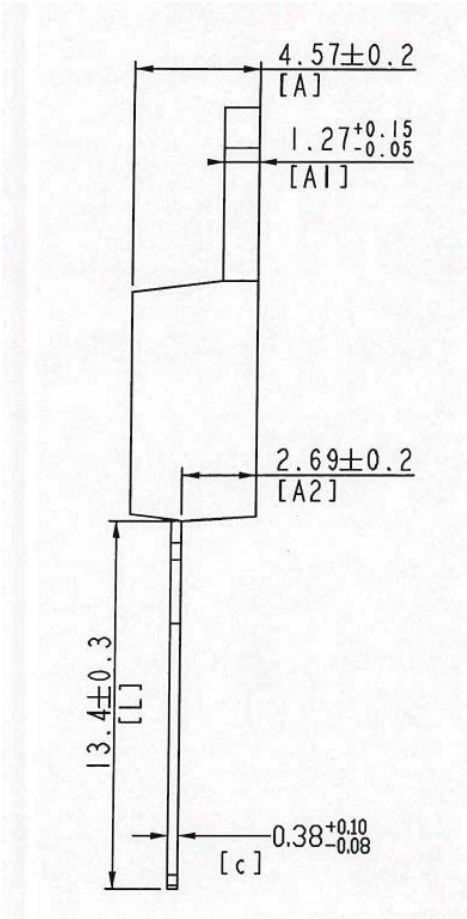
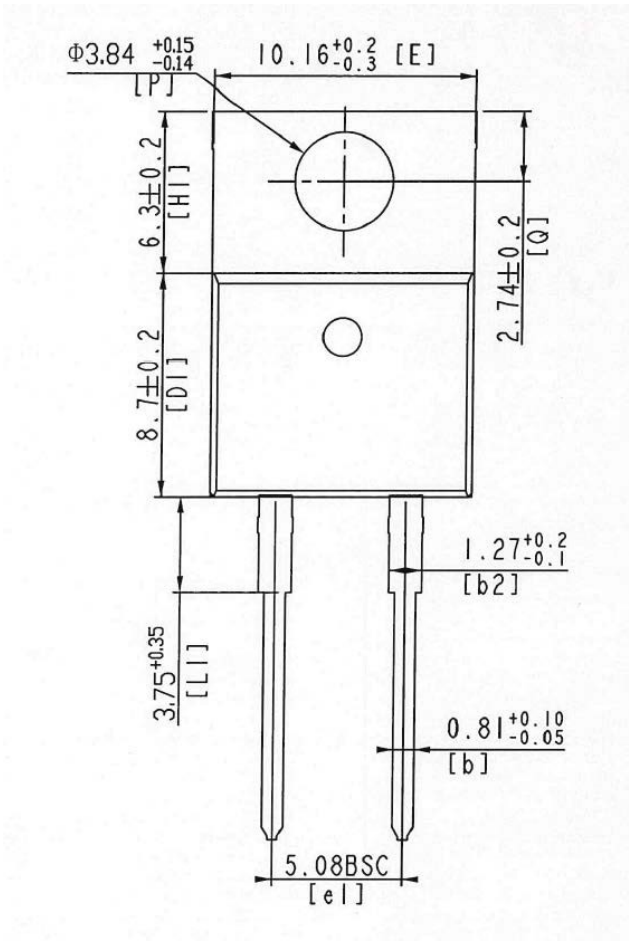


Figure 8. Transient Thermal Impedance



Package Outlines
TO220-2



Package Marking and Ordering Information

Part Number	Top Marking	Package	Packing Method	Quantity
BCH65S04D4	BCH65S04D4	TO220-2	Tube	50 units

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